Anagh Bhaumik

List of Publications by Year
in descending order

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385	12,814	32410	36203
papers	citations	55 h-index	101 g-index

392	392	392	10507
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Emergence of orbital two-channel Kondo effect in epitaxial TiN thin films. Solid State Communications, 2022, 341, 114547.	0.9	1
2	Q-carbon as a new radiation-resistant material. Carbon, 2022, 186, 253-261.	5.4	12
3	Self-organization of amorphous Q-carbon and Q-BN nanoballs. Carbon, 2022, 192, 301-307.	5.4	8
4	Formation of Q-carbon with wafer scale integration. Carbon, 2022, 196, 972-978.	5.4	8
5	Synthesis of multifunctional microdiamonds on stainless steel substrates by chemical vapor deposition. Carbon, 2021, 171, 739-749.	5.4	21
6	Tunable n-Type Conductivity and Transport Properties of Cubic Boron Nitride via Carbon Doping. ACS Applied Electronic Materials, 2021, 3, 1359-1367.	2.0	10
7	Formation of self-organized nano- and micro-diamond rings. Materials Research Letters, 2021, 9, 300-307.	4.1	9
8	Role of Q-carbon in nucleation and formation of continuous diamond film. Carbon, 2021, 176, 558-568.	5.4	19
9	Advances in laser-assisted conversion of polymeric and graphitic carbon into nanodiamond films. Nanotechnology, 2021, 32, .	1.3	12
10	Discovery of double helix of screw dislocations: a perspective. Materials Research Letters, 2021, 9, 453-457.	4.1	4
11	Evidence of weak antilocalization in epitaxial TiN thin films. Journal of Magnetism and Magnetic Materials, 2020, 498, 166094.	1.0	9
12	Nonequilibrium Structural Evolution of Q-Carbon and Interfaces. ACS Applied Materials & Interfaces, 2020, 12, 1330-1338.	4.0	23
13	Direct conversion of Teflon into nanodiamond films. Materials Research Letters, 2020, 8, 408-416.	4.1	7
14	Electron mobility modulation in graphene oxide by controlling carbon melt lifetime. Carbon, 2020, 170, 327-337.	5.4	32
15	Nanometer-Thick Hexagonal Boron Nitride Films for 2D Field-Effect Transistors. ACS Applied Nano Materials, 2020, 3, 7930-7941.	2.4	5
16	Conversion of h-BN into c-BN for tuning optoelectronic properties. Materials Advances, 2020, 1, 830-836.	2.6	9
17	Selective Liquid-Phase Regrowth of Reduced Graphene Oxide, Nanodiamond, and Nanoscale Q-Carbon by Pulsed Laser Annealing for Radiofrequency Devices. ACS Applied Nano Materials, 2020, 3, 5178-5188.	2.4	4
18	Fabrication of ultrahard Q-carbon nanocoatings on AISI 304 and 316 stainless steels and subsequent formation of high-quality diamond films. Diamond and Related Materials, 2020, 104, 107742.	1.8	17

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19	Structural evolution of laser-irradiated ultrananocrystalline diamond/amorphous carbon composite films prepared by coaxial arc plasma. Applied Physics Express, 2020, 13, 105503.	1.1	17
20	Pseudo-topotactic growth of diamond nanofibers. Acta Materialia, 2019, 178, 179-185.	3.8	12
21	Non-equilibrium processing of ferromagnetic heavily reduced graphene oxide. Carbon, 2019, 153, 663-673.	5.4	15
22	Laser-induced structure transition of diamond-like carbon coated on cemented carbide and formation of reduced graphene oxide. MRS Communications, 2019, 9, 910-915.	0.8	12
23	Scale-up of Qâ€'carbon and nanodiamonds by pulsed laser annealing. Diamond and Related Materials, 2019, 99, 107531.	1.8	20
24	Nano-to-micro diamond formation by nanosecond pulsed laser annealing. Journal of Applied Physics, 2019, 126, 125307.	1.1	8
25	Formation of Q-carbon and diamond coatings on WC and steel substrates. Diamond and Related Materials, 2019, 98, 107515.	1.8	10
26	Direct conversion of carbon nanofibers and nanotubes into diamond nanofibers and the subsequent growth of large-sized diamonds. Nanoscale, 2019, 11, 2238-2248.	2.8	31
27	Formation and characterization of nano- and microstructures of twinned cubic boron nitride. Physical Chemistry Chemical Physics, 2019, 21, 1700-1710.	1.3	9
28	Reduced Graphene Oxide/Amorphous Carbon Pâ€"N Junctions: Nanosecond Laser Patterning. ACS Applied Materials & Interfaces, 2019, 11, 24318-24330.	4.0	18
29	Emergence of shallow energy levels in B-doped Q-carbon: A high-temperature superconductor. Acta Materialia, 2019, 174, 153-159.	3.8	10
30	Synthesis of diamond nanostructures from carbon nanotube and formation of diamond-CNT hybrid structures. Carbon, 2019, 150, 388-395.	5.4	40
31	Structureâ€"property correlations in phase-pure B-doped Q-carbon high-temperature superconductor with a record T_c = 55 K. Nanoscale, 2019, 11, 9141-9154.	2.8	5
32	Direct conversion of carbon nanofibers into diamond nanofibers using nanosecond pulsed laser annealing. Physical Chemistry Chemical Physics, 2019, 21, 7208-7219.	1.3	4
33	Electrical Transition in Isostructural VO2 Thin-Film Heterostructures. Scientific Reports, 2019, 9, 3009.	1.6	28
34	Search for near room-temperature superconductivity in B-doped Q-carbon. Materials Research Letters, 2019, 7, 164-172.	4.1	9
35	Room-temperature ferromagnetism in epitaxial titanium nitride thin films. Acta Materialia, 2019, 166, 221-230.	3.8	23
36	Vacancy-Driven Robust Metallicity of Structurally Pinned Monoclinic Epitaxial VO₂ Thin Films. ACS Applied Materials & Interfaces, 2019, 11, 3547-3554.	4.0	27

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37	Reduced Graphene Oxide-Nanostructured Silicon Photosensors with High Photoresponsivity at Room Temperature. ACS Applied Nano Materials, 2019, 2, 2086-2098.	2.4	5
38	Tunable charge states of nitrogen-vacancy centers in diamond for ultrafast quantum devices. Carbon, 2019, 142, 662-672.	5.4	30
39	Diamond film growth by HFCVD on Q-carbon seeded substrate. Carbon, 2019, 141, 182-189.	5.4	19
40	Electron field emission from Q-carbon. Diamond and Related Materials, 2018, 86, 71-78.	1.8	35
41	High temperature superconductivity in distinct phases of amorphous B-doped Q-carbon. Journal of Applied Physics, 2018, 123, .	1.1	17
42	Room-Temperature Ferromagnetism and Extraordinary Hall Effect in Nanostructured Q-Carbon: Implications for Potential Spintronic Devices. ACS Applied Nano Materials, 2018, 1, 807-819.	2.4	46
43	Polarized neutron reflectivity studies on epitaxial BiFeO3/La0.7Sr0.3MnO3 heterostructure integrated with Si (100). AIP Advances, 2018, 8, 055821.	0.6	0
44	Synthesis and Characterization of Quenched and Crystalline Phases: Q-Carbon, Q-BN, Diamond and Phase-Pure c-BN. Jom, 2018, 70, 456-463.	0.9	7
45	Structural Evolution of Q-Carbon and Nanodiamonds. Jom, 2018, 70, 450-455.	0.9	27
46	Q-carbon harder than diamond. MRS Communications, 2018, 8, 428-436.	0.8	36
47	Large-area diamond thin film on Q-carbon coated crystalline sapphire by HFCVD. Journal of Crystal Growth, 2018, 504, 17-25.	0.7	32
48	Enhanced mechanical properties of Q-carbon nanocomposites by nanosecond pulsed laser annealing. Nanotechnology, 2018, 29, 45LT02.	1.3	34
49	Stability of electron field emission in Q-carbon. MRS Communications, 2018, 8, 1343-1351.	0.8	19
50	Magnetic relaxation and three-dimensional critical fluctuations in B-doped Q-carbon â€“ a high-temperature superconductor. Nanoscale, 2018, 10, 12665-12673.	2.8	6
51	Progress in Q-carbon and related materials with extraordinary properties. Materials Research Letters, 2018, 6, 353-364.	4.1	59
52	Electrochromic effect in Q-carbon. Applied Physics Letters, 2018, 112, .	1.5	10
53	Undercooling driven growth of Q-carbon, diamond, and graphite. MRS Communications, 2018, 8, 533-540.	0.8	29
54	High-Temperature Superconductivity in Boron-Doped Q-Carbon. ACS Nano, 2017, 11, 5351-5357.	7.3	49

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55	Conversion of p to n-type reduced graphene oxide by laser annealing at room temperature and pressure. Journal of Applied Physics, 2017, 121, .	1.1	55
56	A novel high-temperature carbon-based superconductor: B-doped Q-carbon. Journal of Applied Physics, 2017, 122, .	1.1	22
57	Discovery of High-Temperature Superconductivity (T_c = 55 K) in B-Doped Q-Carbon. ACS Nano, 2017, 11, 11915-11922.	7.3	60
58	Novel synthesis and properties of pure and NV-doped nanodiamonds and other nanostructures. Materials Research Letters, 2017, 5, 242-250.	4.1	22
59	Discovery of Q-BN and Direct Conversion of h-BN into c-BN and Formation of Epitaxial c-BN/Diamond Heterostructures. MRS Advances, 2016, 1, 2573-2584.	0.5	2
60	Epitaxial integration of TiO2 with Si(100) through a novel approach of oxidation of TiN/Si(100) epitaxial heterostructure. MRS Advances, 2016, 1, 2629-2634.	0.5	7
61	Research Update: Direct conversion of h-BN into pure c-BN at ambient temperatures and pressures in air. APL Materials, 2016, 4, .	2.2	34
62	Ferromagnetic oxide heterostructures on silicon. MRS Communications, 2016, 6, 234-240.	0.8	4
63	Wafer scale integration of reduced graphene oxide by novel laser processing at room temperature in air. Journal of Applied Physics, 2016, 120, .	1.1	21
64	Direct conversion of h-BN into c-BN and formation of epitaxial c-BN/diamond heterostructures. Journal of Applied Physics, 2016, 119, .	1.1	31
65	Enhanced Coercivity in BiFeO3/SrRuO3 heterostructures. MRS Advances, 2016, 1, 597-602.	0.5	1
66	Q-carbon discovery and formation of single-crystal diamond nano- and microneedles and thin films. Materials Research Letters, 2016, 4, 118-126.	4.1	22
67	Strain induced room temperature ferromagnetism in epitaxial magnesium oxide thin films. Journal of Applied Physics, 2015, 118, 165309.	1.1	7
68	Microstructure and transport properties of epitaxial topological insulator Bi2Se3 thin films grown on MgO (100), Cr2O3 (0001), and Al2O3 (0001) templates. Journal of Applied Physics, 2015, 118, .	1.1	12
69	Novel phase of carbon, ferromagnetism, and conversion into diamond. Journal of Applied Physics, 2015, 118, .	1.1	133
70	Research Update: Direct conversion of amorphous carbon into diamond at ambient pressures and temperatures in air. APL Materials, 2015, 3, .	2.2	45
71	Alloying effect on grain-size dependent deformation twinning in nanocrystalline Cuâ€“Zn alloys. Philosophical Magazine, 2015, 95, 301-310.	0.7	22
72	Room temperature ferromagnetism in epitaxial Cr2O3 thin films grown on r-sapphire. Journal of Applied Physics, 2015, 117, 193907.	1.1	19

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73	Macroscopic Twinning Strain in Nanocrystalline Cu. Materials Research Letters, 2014, 2, 63-69.	4.1	31
74	A microstructural approach toward the effect of thickness on semiconductor-to-metal transition characteristics of VO2 epilayers. Journal of Applied Physics, 2014, 115, .	1.1	36
75	Oxygen vacancy enhanced room-temperature ferromagnetism in Sr3SnO/c-YSZ/Si (001) heterostructures. MRS Communications, 2014, 4, 7-13.	0.8	28
76	Tunable electronic structure in dilute magnetic semiconductor Sr3SnO/c-YSZ/Si (001) epitaxial heterostructures. Journal of Applied Physics, 2014, 116, 164903.	1.1	12
77	Evidence for topological surface states in epitaxial Bi 2 Se 3 thin film grown by pulsed laser deposition through magneto-transport measurements. Current Opinion in Solid State and Materials Science, 2014, 18, 279-285.	5.6	34
78	Significant enhancement of optical absorption through nano-structuring of copper based oxide semiconductors: possible future materials for solar energy applications. Physical Chemistry Chemical Physics, 2014, 16, 11054-11066.	1.3	64
79	Epitaxial integration of dilute magnetic semiconductor Sr3SnO with Si (001). Applied Physics Letters, 2013, 103, .	1.5	36
80	Grain size effect on twin density in as-deposited nanocrystalline Cu film. Philosophical Magazine, 2013, 93, 4355-4363.	0.7	16
81	Grain size effect on deformation twinning and detwinning. Journal of Materials Science, 2013, 48, 4467-4475.	1.7	132
82	Ultrafast switching in wetting properties of TiO2/YSZ/Si(001) epitaxial heterostructures induced by laser irradiation. Journal of Applied Physics, 2013, 113, 063706.	1.1	31
83	Field-assisted selective-melt sintering: a novel approach to high-density ceramics. MRS Communications, 2013, 3, 139-143.	0.8	1
84	Role of substrate crystallographic characteristics on structure and properties of rutile TiO2 epilayers. Journal of Applied Physics, 2013, 114, 044314.	1.1	9
85	Enhanced photocatalytic efficiency in zirconia buffered n-NiO/p-NiO single crystalline heterostructures by nanosecond laser treatment. Journal of Applied Physics, 2013, 113, .	1.1	29
86	Domain epitaxy in TiO2/Î±-Al2O3 thin film heterostructures with Ti2O3 transient layer. Applied Physics Letters, 2012, 100, .	1.5	29
87	Epitaxial VO2/Cr2O3/sapphire heterostructure for multifunctional applications. Applied Physics Letters, 2011, 98, .	1.5	20
88	Intrinsic Room-Temperature Ferromagnetic Properties of Ni-Doped ZnO Thin Films. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2011, 42, 3250-3254.	1.1	3
89	Role of interfacial transition layers in VO2/Al2O3 heterostructures. Journal of Applied Physics, 2011, 110, .	1.1	66
90	Atomic structure of misfit dislocations in nonpolar ZnO/Al2O3 heterostructures. Applied Physics Letters, 2010, 97, 121914.	1.5	14

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91	Semiconductor-metal transition characteristics of VO2 thin films grown on c- and r-sapphire substrates. Journal of Applied Physics, 2010, 107, .	1.1	124
92	Role of twin boundaries in semiconductor to metal transition characteristics of VO2 films. Applied Physics Letters, 2010, 97, .	1.5	22
93	Effect of Li doping in NiO thin films on its transparent and conducting properties and its application in heteroepitaxial p-n junctions. Journal of Applied Physics, 2010, 108, .	1.1	138
94	Twinning partial multiplication at grain boundary in nanocrystalline fcc metals. Applied Physics Letters, 2009, 95, .	1.5	104
95	MoOx modified ZnGaO based transparent conducting oxides. Journal of Applied Physics, 2009, 105, 053704.	1.1	7
96	Semiconductor to metal transition characteristics of VO2 thin films grown epitaxially on Si (001). Applied Physics Letters, 2009, 95, .	1.5	72
97	The synthesis and magnetic properties of a nanostructured Ni-MgO system. Jom, 2009, 61, 76-81.	0.9	8
98	Defect dependent ferromagnetism in MgO doped with Ni and Co. Applied Physics Letters, 2008, 93, .	1.5	39
99	Observation of room temperature ferromagnetism in Ga:ZnO: A transition metal free transparent ferromagnetic conductor. Applied Physics Letters, 2008, 93, .	1.5	37
100	Deformation twin formed by self-thickening, cross-slip mechanism in nanocrystalline Ni. Applied Physics Letters, 2008, 93, .	1.5	30
101	Growth of biepitaxial zinc oxide thin films on silicon (100) using yttria-stabilized zirconia buffer layer. Applied Physics Letters, 2008, 93, 251905.	1.5	15
102	Structure-magnetic property correlations in the epitaxial FePt system. Applied Physics Letters, 2008, 92, .	1.5	43
103	Epitaxial growth and magnetic properties of La0.7Sr0.3MnO3 films on (0001) sapphire. Applied Physics Letters, 2007, 90, 101903.	1.5	13
104	Anisotropic magnetic properties in [110] oriented epitaxial La0.7Sr0.3MnO3 films on (0001) sapphire. Journal of Applied Physics, 2007, 102, 013527.	1.1	4
105	Nanostructured GaN Nucleation Layer for Light-Emitting Diodes. Journal of Nanoscience and Nanotechnology, 2007, 7, 2719-2725.	0.9	4
106	Structural, Magnetic, and Electron Transport Studies on Nanocrystalline Layered Manganite La1.2Ba1.8Mn2O7 System. Journal of Nanoscience and Nanotechnology, 2007, 7, 965-969.	0.9	8
107	Gallium-doped zinc oxide films as transparent electrodes for organic solar cell applications. Journal of Applied Physics, 2007, 102, .	1.1	140
108	Metallic conductivity and metal-semiconductor transition in Ga-doped ZnO. Applied Physics Letters, 2006, 88, 032106.	1.5	248

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109	Electrical properties of transparent and conducting Ga doped ZnO. Journal of Applied Physics, 2006, 100, 033713.	1.1	259
110	Microstructure and electrical property correlations in Ga:ZnO transparent conducting thin films. Journal of Applied Physics, 2006, 100, 093519.	1.1	44
111	Transmission electron microscopy observations on the microstructure of naturally aged Alâ€“Mgâ€“Si alloy AA6022 processed with an electric field. Journal of Materials Science, 2006, 41, 7555-7561.	1.7	8
112	Epitaxial ZnO/Pt layered structures and ZnO-Pt nanodot composites on sapphire (0001). Journal of Electronic Materials, 2006, 35, 840-845.	1.0	4
113	Epitaxial growth and properties of MoOx(2<x<2.75) films. Journal of Applied Physics, 2005, 97, 083539.	1.1	132
114	Enhanced photoconductivity of ZnO films Co-doped with nitrogen and tellurium. Applied Physics Letters, 2005, 86, 211918.	1.5	66
115	Effect of UV/VUV Enhanced RTP on Process Variation and Device Performance of Metal Gate/High-<tex>$kappa$</tex>Gate Stacks for the Sub-90-nm CMOS Regime. IEEE Transactions on Semiconductor Manufacturing, 2005, 18, 55-62.	1.4	3
116	Novel Methods of Forming Self-Assembled Nanostructured Materials: Ni Nanodots in Al₂O₃ and TiN Matrices. Journal of Nanoscience and Nanotechnology, 2004, 4, 726-732.	0.9	14
117	Epitaxial GaN on Si(111): Process control of SiNx interlayer formation. Applied Physics Letters, 2004, 85, 133-135.	1.5	24
118	Origin of room-temperature ferromagnetism in cobalt-doped ZnO. Journal of Electronic Materials, 2004, 33, 1298-1302.	1.0	17
119	TaN-TiN binary alloys and superlattices as diffusion barriers for copper interconnections. Journal of Electronic Materials, 2004, 33, L5-L5.	1.0	4
120	Zn0.9Co0.1O-based diluted magnetic semiconducting thin films. Applied Physics Letters, 2004, 84, 5255-5257.	1.5	301
121	TaN-TiN binary alloys and superlattices as diffusion barriers for copper interconnects. Journal of Electronic Materials, 2003, 32, 994-999.	1.0	10
122	Domain epitaxy: A unified paradigm for thin film growth. Journal of Applied Physics, 2003, 93, 278-285.	1.1	515
123	Rectifying electrical characteristics of La0.7Sr0.3MnO3/ZnO heterostructure. Applied Physics Letters, 2003, 83, 1773-1775.	1.5	91
124	Growth and characteristics of TaN/TiN superlattice structures. Applied Physics Letters, 2003, 83, 3072-3074.	1.5	13
125	Effect of microstructure on diffusion of copper in TiN films. Journal of Applied Physics, 2003, 93, 5210-5214.	1.1	32
126	Growth, characterization, and electrical properties of PbZr_{0.52}Ti_{0.48}O₃ thin films on buffered silicon substrates using pulsed laser deposition. Journal of Materials Research, 2003, 18, 111-114.	1.2	14

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127	Growth of epitaxial NdNiO3 and integration with Si(100). Applied Physics Letters, 2002, 80, 1337-1339.	1.5	12
128	Z-contrast imaging of dislocation cores at the GaAs/Si interface. Applied Physics Letters, 2002, 81, 2728-2730.	1.5	40
129	Strain-induced tuning of metalâ€“insulator transition in NdNiO3. Applied Physics Letters, 2002, 80, 4039-4041.	1.5	75
130	Epitaxial growth of TaN thin films on Si(100) and Si(111) using a TiN buffer layer. Applied Physics Letters, 2002, 80, 2323-2325.	1.5	35
131	Copper diffusion characteristics in single-crystal and polycrystalline TaN. Applied Physics Letters, 2002, 81, 1453-1455.	1.5	40
132	Epitaxial growth of ZnO films on Si(111). Journal of Materials Research, 2002, 17, 2480-2483.	1.2	48
133	WEAK-LOCALIZATION EFFECT IN SINGLE CRYSTAL TaN(001) FILMS. Modern Physics Letters B, 2002, 16, 1143-1149.	1.0	5
134	Improved magnetic properties of self-assembled epitaxial nickel nanocrystallites in thin-film ceramic matrix. Journal of Materials Research, 2002, 17, 738-742.	1.2	10
135	Effect of Thickness Variation in High-Efficiency Ingan/Gan Light Emitting Diodes. Materials Research Society Symposia Proceedings, 2002, 743, L6.22.1.	0.1	0
136	Single Crystal TaN Thin Films on TiN/Si Heterostructure. Materials Research Society Symposia Proceedings, 2002, 716, 881.	0.1	0
137	Studies on Epitaxial Relationship and Interface Structure of AlN/Si(111) and GaN/Si(111) Heterostructures. Materials Research Society Symposia Proceedings, 2002, 743, L3.24.1.	0.1	1
138	Structural, optical and electrical properties of the novel semiconductor alloy ZnOxTe(1-x). Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0
139	The Growth and Characterization of Zinc Oxide Thin Film on Fused Silica and SiO2/Si(100) Substrates. Materials Research Society Symposia Proceedings, 2002, 744, 1.	0.1	0
140	Copper Diffusion Characteristics in Single Crystal and Polycrystalline TaN. Materials Research Society Symposia Proceedings, 2002, 745, 6111.	0.1	0
141	Novel Nanostructured Metal and Ceramic Composites. Materials Research Society Symposia Proceedings, 2002, 750, 1.	0.1	0
142	Growth of TiN/AlN Superlattice by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2002, 750, 1.	0.1	1
143	Epitaxial Growth of Magnetic Nickel Nanodots by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2002, 755, 1.	0.1	2
144	Mechanism for grain size softening in nanocrystalline Zn. Applied Physics Letters, 2002, 81, 2241-2243.	1.5	63

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145	Synthesis and atomic-level characterization of Ni nanoparticles in Al2O3 matrix. Applied Physics Letters, 2002, 81, 4204-4206.	1.5	32
146	Growth of epitaxial ZnO films on Si(111). Materials Research Society Symposia Proceedings, 2002, 722, 1071.	0.1	3
147	Z-Contrast Imaging of Dislocation Cores at the Si/GaAs Interface. Microscopy and Microanalysis, 2002, 8, 1604-1605.	0.2	0
148	Structure and Properties of Nanocrystalline Zinc Films. Journal of Nanoparticle Research, 2002, 4, 265-269.	0.8	12
149	Self-Aligned Passivated Copper Interconnects: A Novel Technique for Making Interconnections in Ultra Large Scale Integration Device Applications. Materials Research Society Symposia Proceedings, 2002, 716, 811.	0.1	0
150	Magnetic properties of self-assembled nanoscale La2/3Ca1/3MnO3 particles in an alumina matrix. Applied Physics Letters, 2001, 79, 1327-1329.	1.5	43
151	Laser-ablated plasma for deposition of ZnO thin films on various substrates. Science and Technology of Advanced Materials, 2001, 2, 517-523.	2.8	21
152	Colossal magnetoresistive and ferroelectric thin films deposited by excimer laser induced plasma. Science and Technology of Advanced Materials, 2001, 2, 525-531.	2.8	4
153	Self-assembled epitaxial and polycrystalline magnetic nickel nanocrystallites. Applied Physics Letters, 2001, 79, 2817-2819.	1.5	44
154	Hydrogen Free, High sp3 Content DLC Films Produced by Pulsed Laser Ablation of Amorphous Graphite. Materials Research Society Symposia Proceedings, 2001, 697, 5111.	0.1	0
155	Tunable Magnetic Properties in Metal Ceramic Composite Thin Films. Materials Research Society Symposia Proceedings, 2001, 676, 3171.	0.1	0
156	Pulsed Laser Deposition and Characterization of Zn1âˆ’xMnxO Films. Materials Research Society Symposia Proceedings, 2001, 692, 1.	0.1	0
157	Nickel Nanocomposite Thin Films. Materials Research Society Symposia Proceedings, 2001, 703, 1.	0.1	1
158	Mechanical properties of nanocrystalline and epitaxial TiN films on (100) silicon. Journal of Materials Research, 2001, 16, 2733-2738.	1.2	36
159	Effect of chamber pressure and atmosphere on the microstructure and nanomechanical properties of amorphous carbon films prepared by pulsed laser deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 311-316.	0.9	16
160	Structural and magnetoresistance properties of La2/3Ca1/3MnO3 thin films on buffered silicon substrates. Applied Physics Letters, 2001, 78, 1098-1100.	1.5	15
161	Microstructure and Nanomechanical Properties of Amorphous Carbon Thin Films Prepared by Pulsed Laser Deposition in Various Atmospheres. Materials Research Society Symposia Proceedings, 2000, 616, 217.	0.1	0
162	Novel Nanocrystalline Materials by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2000, 617, 1.	0.1	4

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163	Optical and Structural Characteristics Of Gold Nanocrystallites Embedded in a Dielectric Matrix. Materials Research Society Symposia Proceedings, 2000, 617, 271.	0.1	5
164	Plasma and DLC Film Characteristics from Pulsed Laser Ablation Of Single Crystal Graphite and Amorphous Carbon: A Comparative Study Employing Electrostatic Probe Measurements. Materials Research Society Symposia Proceedings, 2000, 617, 311.	0.1	1
165	Properties of the magnetoresistive La0.8Sr0.2MnO3 film and integration with PbZr0.52 Ti0.48O3 ferroelectrics. Materials Research Society Symposia Proceedings, 2000, 617, 3231.	0.1	0
166	Growth Of ZnO/MgZnO Superlattice On Sapphire. Materials Research Society Symposia Proceedings, 2000, 617, 671.	0.1	8
167	Preparation Of Superhard Functionally Graded Tetrahedral Amorphous Carbon Coatings By Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2000, 617, 771.	0.1	2
168	Novel Tungsten Carbide Nanocrystalline Composites by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2000, 634, 611.	0.1	2
169	Novel Cubic ZnxMg1â^'xO Epitaxial Heterostructures on Si (100) Substrates. Materials Research Society Symposia Proceedings, 2000, 639, 3531.	0.1	0
170	Phase Separation in Multiple ZnO /Cubic- MgxZn1â^'xO Superlattice Heterostructures Observed Via High Resolution Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 2000, 639, 6501.	0.1	0
171	Effect of Film Thickness on the Nanoindentation Measurements of Hard Diamondlike Carbon Films Prepared by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 2000, 649, 7201.	0.1	0
172	Size and Interface Control of Novel Nanocrystalline Materials Using Pulsed Laser Deposition. Journal of Nanoparticle Research, 2000, 2, 91-96.	0.8	21
173	Superhard diamondlike carbon: preparation, theory, and properties. International Materials Reviews, 2000, 45, 133-164.	9.4	85
174	Comparative study of pulsed laser ablated plasma plumes from single crystal graphite and amorphous carbon targets. Part II. Electrostatic probe measurements. Journal of Applied Physics, 2000, 88, 6868-6874.	1.1	12
175	Integration of Pb(Zr0.52Ti0.48)O3 epilayers with Si by domain epitaxy. Applied Physics Letters, 2000, 76, 1458-1460.	1.5	30
176	Microstructure and electrical resistivity of Cu and Cu3Ge thin films on Si1â^'xGex alloy layers. Journal of Applied Physics, 2000, 87, 365-368.	1.1	12
177	Atomic structure, electrical properties, and infrared range optical properties of diamondlike carbon films containing foreign atoms prepared by pulsed laser deposition. Journal of Materials Research, 2000, 15, 633-641.	1.2	26
178	The Inverse Hall-Petch Effectâ€"Fact or Artifact?. Materials Research Society Symposia Proceedings, 2000, 634, 511.	0.1	43
179	Refractive indices and absorption coefficients of MgxZn1â^'xO alloys. Applied Physics Letters, 2000, 76, 979-981.	1.5	191
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